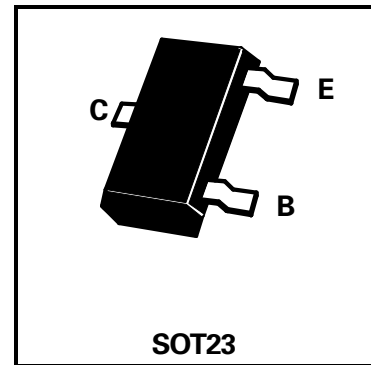


SOT23 PNP SILICON PLANAR SWITCHING TRANSISTORS

ISSUE 2 – SEPTEMBER 95

BSS80B
BSS80C

PARTMARKING DETAIL — BSS80B - CH
BSS80C - CJ



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-800	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{TOT}	330	mW
Operating and Storage Temperature Range	$t_j:t_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER		SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	-60		V	$I_C = -10\mu A$
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	-40		V	$I_C = -10mA$
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	-5			$I_E = -10mA$
Collector Cut-Off Current		I_{CBO}		-10 -10	nA μA	$V_{CB} = -50V$, $V_{CB} = -50V$, $T_a = 150^{\circ}C$
Emitter Cut-Off Current		I_{EBO}		-10	nA	$V_{BE} = -3V$
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$		-0.4 -1.6	mV V	$I_C = -150mA$, $V_{CE} = -10V$ $I_C = -150mA$, $V_{CE} = -10V$
Static Forward Current Transfer Ratio	BSS80B BSS80C	h_{FE}	40 100	120 300		$I_C = 150mA$, $V_{CE} = 10V$ $I_C = 150mA$, $V_{CE} = 10V$
Transition Frequency		f_T	200		MHz	$V_{CE} = -20V$, $I_C = -50mA$ $f = 100MHz$
Output Capacitance		C_{obo}		8	pF	$V_{CB} = -10V$, $f = 1MHz$
Delay Time		t_d		10	ns	$V_{CC} = -30V$, $I_C = -150mA$ $I_{B1} = -I_{B2} = -15mA$
Rise Time		t_r		40	ns	
Storage Time		t_s		80	ns	
Fall Time		t_f		30	ns	